

isc Silicon NPN Power Transistor
2SC2316
DESCRIPTION

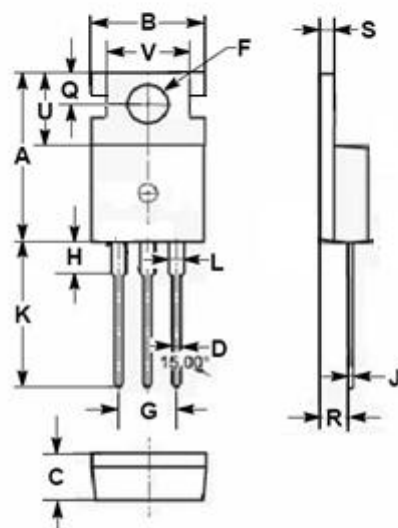
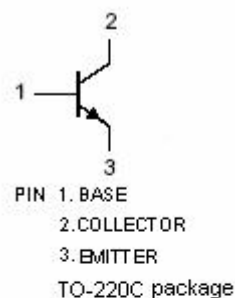
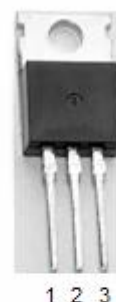
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = 80(V)(Min.)$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Series regulator, switch and general purpose applications

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ C$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	100	V
V_{CEO}	Collector-Emitter Voltage	80	V
V_{EBO}	Emitter-Base Voltage	6	V
I_C	Collector Current-Continuous	6	A
P_C	Total Power Dissipation @ $T_C = 25^\circ C$	50	W
T_J	Junction Temperature	150	$^\circ C$
T_{stg}	Storage Temperature Range	-55~150	$^\circ C$



DIM	mm	
	MIN	MAX
A	15.50	15.90
B	9.80	10.20
C	4.20	4.50
D	0.70	0.90
F	3.40	3.70
G	4.98	5.18
H	2.68	2.90
J	0.44	0.60
K	12.80	13.40
L	1.20	1.45
Q	2.70	2.90
R	2.30	2.70
S	1.29	1.35
U	6.45	6.65
V	8.66	8.86

isc Silicon NPN Power Transistor**2SC2316****ELECTRICAL CHARACTERISTICS****T_C=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = 25mA; I _B = 0	80			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = 3A; I _B = 60mA			1.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = 100V; I _E = 0			0.1	mA
I _{EBO}	Emitter Cutoff Current	V _{EB} = 6V; I _C = 0			0.1	mA
h _{FE}	DC Current Gain	I _C = 0.5A; V _{CE} = 4V	500			
f _T	Current-Gain—Bandwidth Product	I _E = 100mA; V _{CE} = 12V		30		MHz